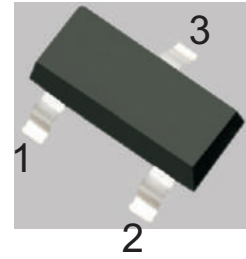


MMBT2222A
NPN TRANSISTOR

FEATURES

- Epitaxial planar die construction
- Complementary PNP Type available(MMBT2907A)

SOT-23



1.BASE
2.EMITTER
3.COLLECTOR

MAXIMUM RATINGS (Ta=25°C unless otherwise noted)

Parameter	Symbol	Value	Unit
Collector-Base Voltage	V_{CB0}	75	V
Collector-Emitter Voltage	V_{CEO}	40	V
Emitter-Base Voltage	V_{EBO}	6	V
Collector Current — Continuous	I_C	600	mA
Collector Power Dissipation	P_C	300	mW
Thermal Resistance From Junction To Ambient	R_{thJA}	417	°C/W
Operation Junction and Storage Temperature Range	T_J, T_{stg}	-55~+150	°C

CLASSIFICATION OF h_{FE}

Rank	L	H
Range	100-200	200-300
Marking	1P	

ELECTRICAL CHARACTERISTICS (TA = 25°C unless otherwise noted.)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = 10\mu A, I_E = 0$	75			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = 10\text{ mA}, I_B = 0$	40			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = 10\mu A, I_C = 0$	6			V
Collector cut-off current	I_{CBO}	$V_{CB} = 60V, I_E = 0$			0.01	μA
Collector cut-off current	I_{CEX}	$V_{CE} = 30V, V_{BE(off)} = 3V$			0.01	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = 3V, I_C = 0$			0.1	μA
DC current gain	h_{FE1}	$V_{CE} = 10V, I_C = 150\text{mA}$	100		300	
	h_{FE2}	$V_{CE} = 10V, I_C = 0.1\text{mA}$	40			
	h_{FE3}	$V_{CE} = 10V, I_C = 500\text{mA}$	42			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = 500\text{mA}, I_B = 50\text{mA}$			1.0 0.3	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C = 150\text{mA}, I_B = 15\text{mA}$			2.0 1.2	V
Transition frequency	f_T	$V_{CE} = 20V, I_C = 20\text{mA}, f = 100\text{MHz}$	300			MHz
Delay time	t_d	$V_{CC} = 30V, V_{BE(off)} = -0.5V, I_C = 150\text{mA}, I_{B1} = 15\text{mA}$			10	ns
Rise time	t_r				25	ns
Storage time	t_s	$V_{CC} = 30V, I_C = 150\text{mA}, I_{B1} = -I_{B2} = 15\text{mA}$			225	ns
Fall time	t_f				60	ns